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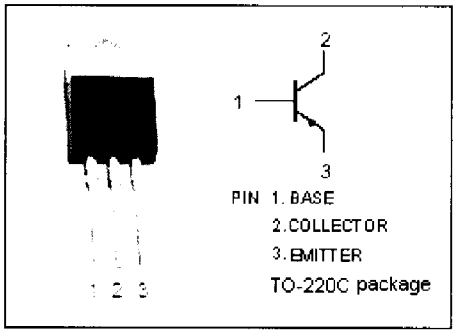
Silicon PNP Power Transistor — 2SA740

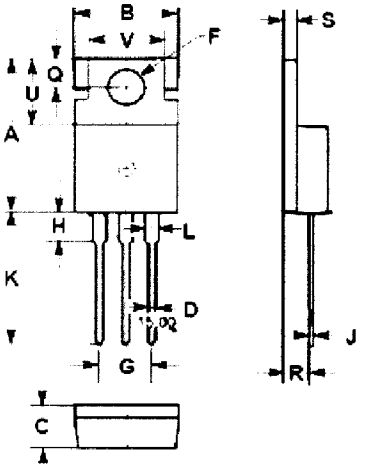


DESCRIPTION

- Collector-Emitter Breakdown Voltage
  : $V_{(BR)CEO}$= -150V(Min)
- DC Current Gain
  : h_{FE}= 40-140@ I_C= -0.5A
- Complementary to Type 2SC1448

APPLICATIONS

- Power amplifier applications.
- Vertical output applications.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_E	Emitter Current-Continuous	1.5	A
P_C	Total Power Dissipation @ T_a=25℃	1.5	W
	Total Power Dissipation @ T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-150			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA ; I_E= 0	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA ; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A ; V_{CE}= -10V			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V ; I_E= 0			-20	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μ A
h_{FE}	DC Current Gain	I_C= -0.5A ; V_{CE}= -10V	40		140	
C_{OB}	Output Capacitance	I_E= -0; V_{CB}= -10V; f_{test}= 1MHz		90		pF
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A;V_{CE}= -10V		8		MHz